CLAIMS

WHAT IS CLAIMED IS:

[CLAIM 1]

A semiconductor structure, comprising:

a first semiconductor substrate;

a first conductive layer located on the first semiconductor substrate and comprising:

a main body portion; and

an extension portion connected to the main body portion and comprising a terminal portion away from the main body portion; and

first bonding pads connected to the main body portion and the extension portion, wherein the number of the first bonding pads connected to the terminal portion of the extension portion is plural.

[CLAIM 2]

The semiconductor structure according to claim 1, wherein the number of the first bonding pads connected to the extension portion is less than the number of the first bonding pads connected to the main body portion.

[CLAIM 3]

The semiconductor structure according to claim 1, wherein the number of the first bonding pads connected to the terminal portion of the extension portion is less than the number of the first bonding pads connected to the main body portion.

[CLAIM 4]

The semiconductor structure according to claim 1, wherein a width of the terminal portion of the extension portion is greater than a width of the rest of the extension portion.

[CLAIM 5]

The semiconductor structure according to claim 1, wherein the first bonding pads connected to the terminal portion of the extension portion are arranged in a single direction.

[CLAIM 6]

The semiconductor structure according to claim 1, wherein the first bonding pads connected to the terminal portion of the extension portion are arranged in an array.

[CLAIM 7]

The semiconductor structure according to claim 1, further comprising:

a first dielectric layer located on the first semiconductor substrate, wherein the first conductive layer and the first bonding pads are located in the first dielectric layer.

[CLAIM 8]

The semiconductor structure according to claim 7, further comprising:

at least one second conductive layer located on the first semiconductor substrate; and

second bonding pads connected to the second conductive layer.

[CLAIM 9]

The semiconductor structure according to claim 8, wherein the second conductive layer is adjacent to the terminal portion of the extension portion.

[CLAIM 10]

The semiconductor structure according to claim 8, wherein the second conductive layer and the second bonding pads are located in the first dielectric layer.

[CLAIM 11]

The semiconductor structure according to claim 8, further comprising:

a second semiconductor substrate, wherein the first semiconductor substrate is located on the second semiconductor substrate;

a third conductive layer located on the second semiconductor substrate; and

third bonding pads connected to the third conductive layer, wherein a portion of the first bonding pads is bonded to the third bonding pads.

[CLAIM 12]

The semiconductor structure according to claim 11, further comprising:

a second dielectric layer located on the second semiconductor substrate, wherein the third conductive layer and the third bonding pads are located in the second dielectric layer, and

the first dielectric layer is bonded to the second dielectric layer.

[CLAIM 13]

The semiconductor structure according to claim 12, further comprising:

at least one fourth conductive layer located on the second semiconductor substrate; and

fourth bonding pads connected to the fourth conductive layer,

wherein a portion of the first bonding pads is bonded to a portion of the fourth bonding pads, and the second bonding pads are bonded to another portion of the fourth bonding pads.

[CLAIM 14]

The semiconductor structure according to claim 13, wherein the fourth conductive layer and the fourth bonding pads are located in the second dielectric layer.

[CLAIM 15]

The semiconductor structure according to claim 13, wherein

a portion of a vertical projection of the first conductive layer falls on the third conductive layer,

another portion of the vertical projection of the first conductive layer falls on the fourth conductive layer, and

a portion of a vertical projection of the second conductive layer falls on the fourth conductive layer.

[CLAIM 16]

The semiconductor structure according to claim 13, further comprising:

at least one fifth conductive layer located on the second semiconductor substrate; and

at least one fifth bonding pad, wherein the fifth bonding pad is connected to the fifth conductive layer,

wherein a portion of the first bonding pads is bonded to the fifth bonding pad.